优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码　企业QQ二维码

Product Summary

Device	BV_{DSS}	$R_{DS(ON)}$	I_D T_A = +25°C
Q1	30V	460mΩ @ V_{GS} = 4.5V	1.1A
		560mΩ @ V_{GS} = 2.5V	1.0A
Q2	-30V	1000mΩ @ V_{GS} = -4.5V	-0.7A
		1500mΩ @ V_{GS} = -2.5V	-0.6A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

Applications

- Backlighting
- DC-DC converters
- Power-management functions

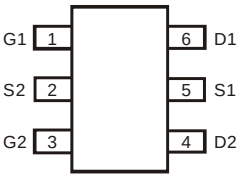
Mechanical Data

- Package: TSOT26
- Package Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.013 grams (Approximate)

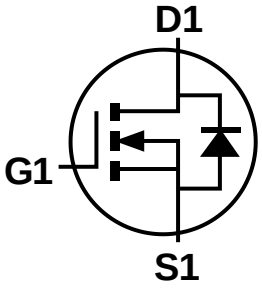
e3

TSOT26

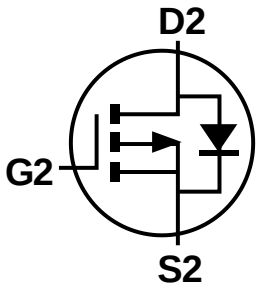
Top View



Top View



Q1 N-Channel



Q2 P-Channel

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Q1 Value	Q2 Value	Unit
Drain-Source Voltage			V_{DSS}	30	-30	V
Gate-Source Voltage			V_{GSS}	±8	±8	V
Continuous Drain Current (Note 6) V_{GS} = 4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	1.1 0.9	-0.7 -0.6	A
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	0.73	-0.68	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I_{DM}	2.6	-1.9	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_D	0.54	W
Thermal Resistance, Junction to Ambient @T_A = +25°C (Note 5)	$R_{\theta JA}$	230	°C/W
Power Dissipation (Note 6)	P_D	0.83	W
Thermal Resistance, Junction to Ambient @T_A = +25°C (Note 6)	$R_{\theta JA}$	150	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics – Q1 N-Channel (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	V_{GS} = 0V, I_D = 10μA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	V_{DS} = 30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±10	μA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.45	—	0.95	V	V_{DS} = V_{GS}, I_D = 250μA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	290 340 400	460 560 730	mΩ	V_{GS} = 4.5V, I_D = 200mA V_{GS} = 2.5V, I_D = 100mA V_{GS} = 1.8V, I_D = 75mA
Diode Forward Voltage	V_{SD}	—	0.6	1.2	V	V_{DS} = V_{GS}, I_D = 300mA
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	40.8	—	pF	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	7.6	—		
Reverse Transfer Capacitance	C_{rss}	—	4.6	—		
Total Gate Charge	Q_{gs}	—	0.9	—	nC	V_{GS} = 4.5V, V_{DS} = 15V, I_D = 1A
Gate-Source Charge	Q_{gd}	—	0.05	—		
Gate-Drain Charge	C_{iss}	—	0.3	—		
Turn-On Delay Time	$t_{D(ON)}$	—	1.1	—	ns	V_{DS} = 10V, I_D = 1A V_{GS} = 4.5V, R_G = 6Ω
Turn-On Rise Time	t_R	—	15.9	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	20.7	—		
Turn-Off Fall Time	t_F	—	20.0	—		

Notes:
5. Device mounted on FR-4 substrate PCB, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PCB, 2oz copper, with 1inch square copper plate.
7. Repetitive rating, pulse width limited by junction temperature.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to production testing.

Electrical Characteristics – Q2 P-Channel (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-30	—	—	V	V_{GS} = 0V, I_D = -250μA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1	μA	V_{DS} = -30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±10	μA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	-0.5	—	-1.1	V	V_{DS} = V_{GS}, I_D = -250μA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	0.72 0.86 1.0	1 1.5 2	Ω	V_{GS} = -4.5V, I_D = -400mA V_{GS} = -2.5V, I_D = -200mA V_{GS} = -1.8V, I_D = -100mA
Diode Forward Voltage	V_{SD}	—	-0.9	-1.2	V	V_{GS} = 0V, I_S = -300mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	54	—	pF	V_{DS} = -15V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	10.9	—		
Reverse Transfer Capacitance	C_{rss}	—	5.8	—		
Total Gate Charge	Q_g	—	1.0	—	nC	V_{GS} = -4.5V, V_{DS} = -15V, I_D = -1A
Total Gate Charge	Q_g	—	1.6	—		V_{GS} = -8V, V_{DS} = -15V I_D = -1A
Gate-Source Charge	Q_{gs}	—	0.2	—		
Gate-Drain Charge	Q_{gd}	—	0.1	—		
Turn-On Delay Time	$t_{D(ON)}$	—	3.8	—	ns	V_{DD} = -10V, R_L = 10Ω V_{GS} = -4.5V, R_G = 6Ω
Turn-On Rise Time	t_R	—	11	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	45	—		
Turn-Off Fall Time	t_F	—	20	—		

Notes: 7. Repetitive rating, pulse width limited by junction temperature.
8. Short duration pulse test used to minimize self-heating effect.

Q1 N-Channel

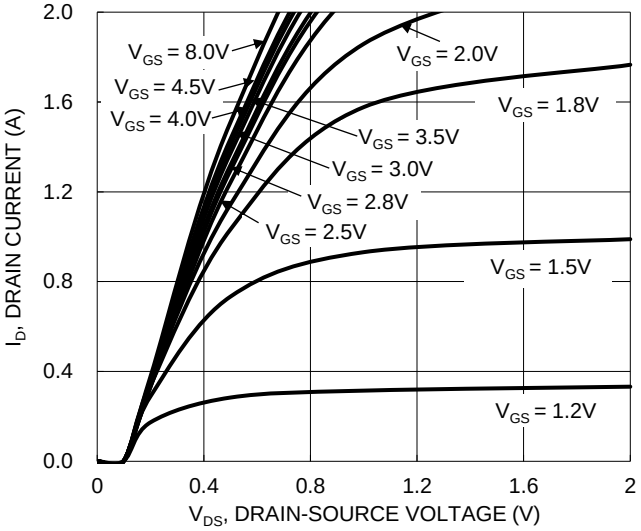


Figure 1. Typical Output Characteristic

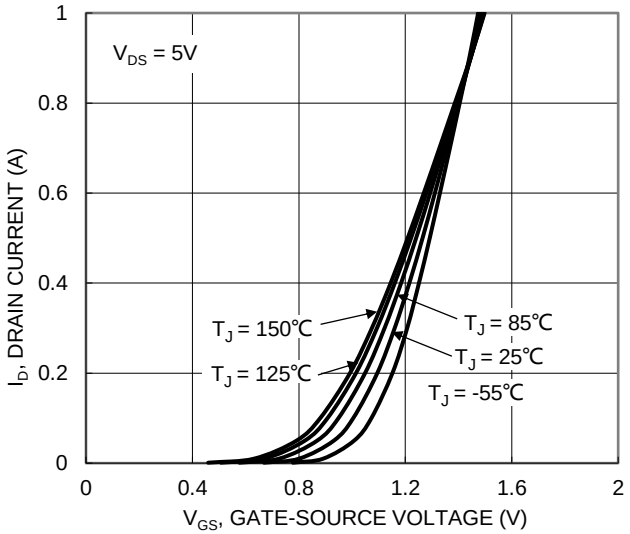


Figure 2. Typical Transfer Characteristic

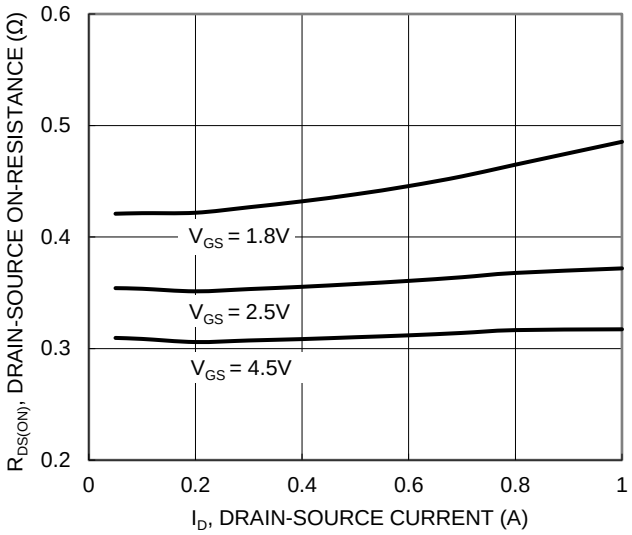


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

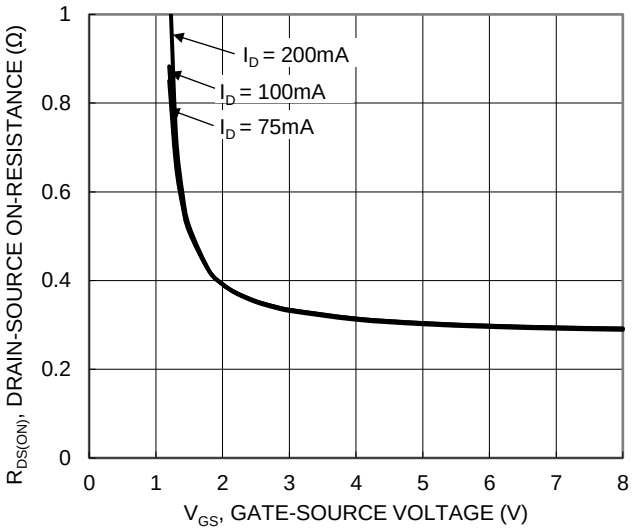


Figure 4. Typical Transfer Characteristic

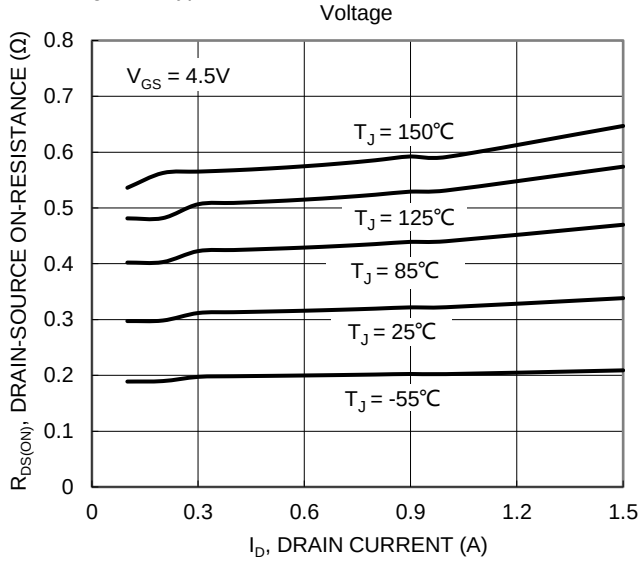


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

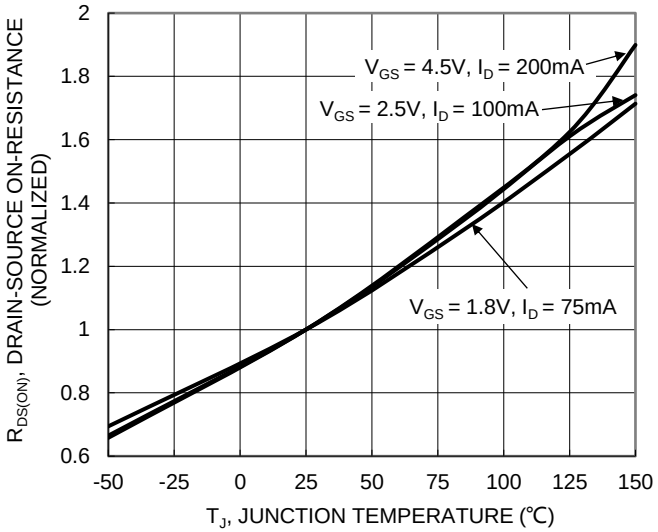


Figure 6. On-Resistance Variation with Junction Temperature

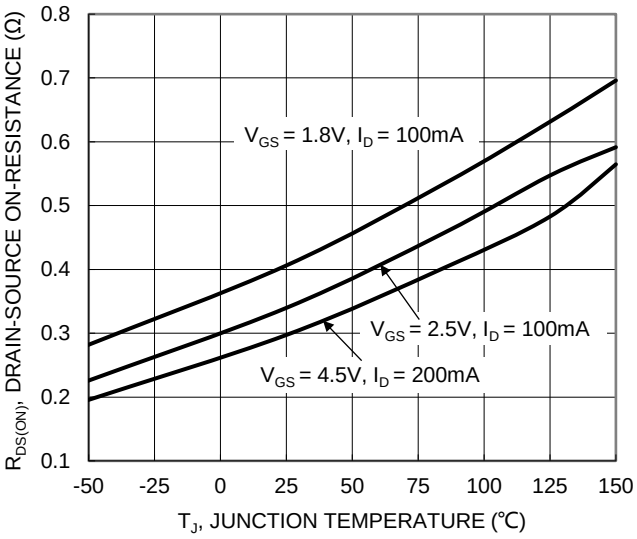


Figure 7. On-Resistance Variation with Junction Temperature

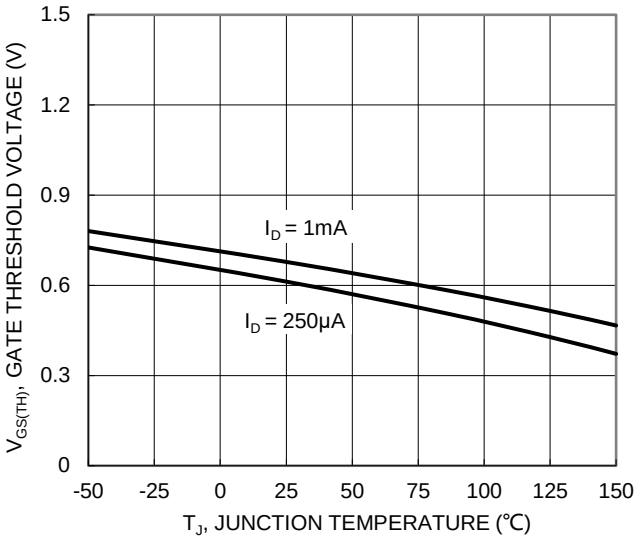


Figure 8. Gate Threshold Variation vs. Junction Temperature

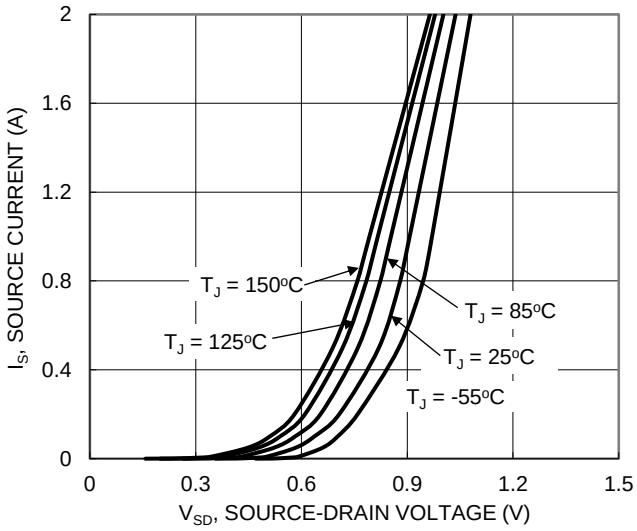


Figure 9. Diode Forward Voltage vs. Current

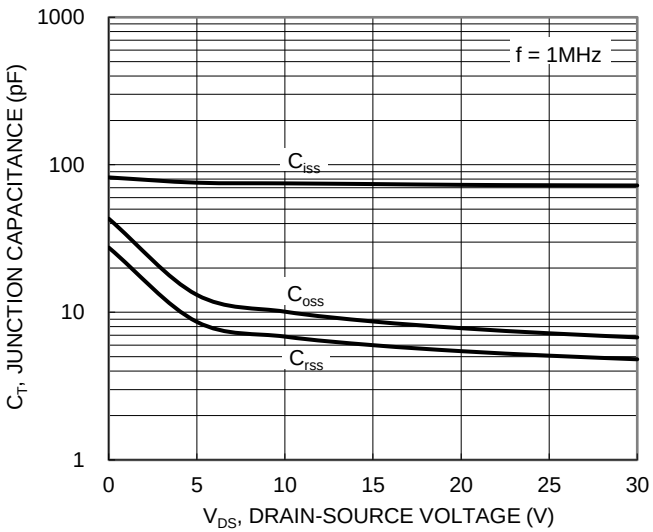


Figure 10. Typical Junction Capacitance

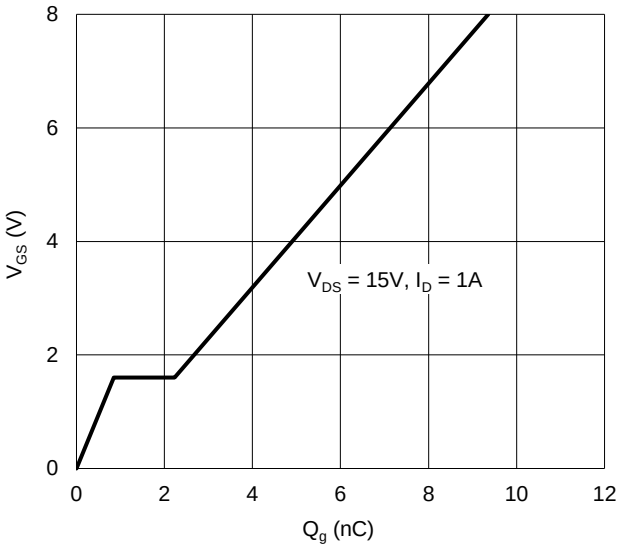


Figure 11. Gate Charge

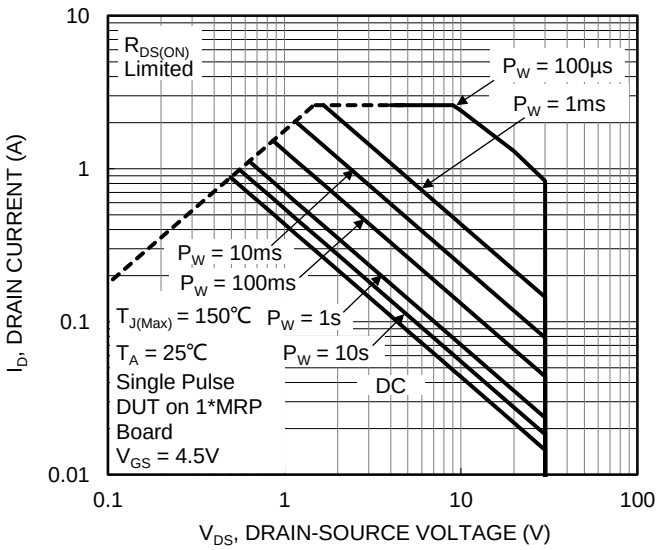


Figure 12. SOA, Safe Operation Area

Q2 P-Channel

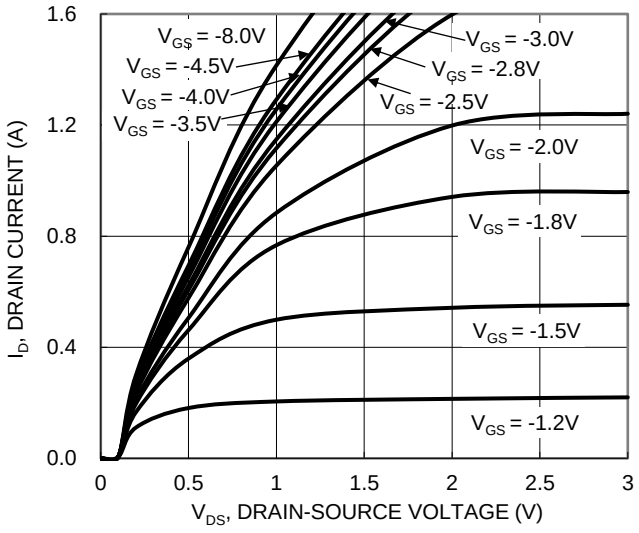


Figure 13. Typical Output Characteristic

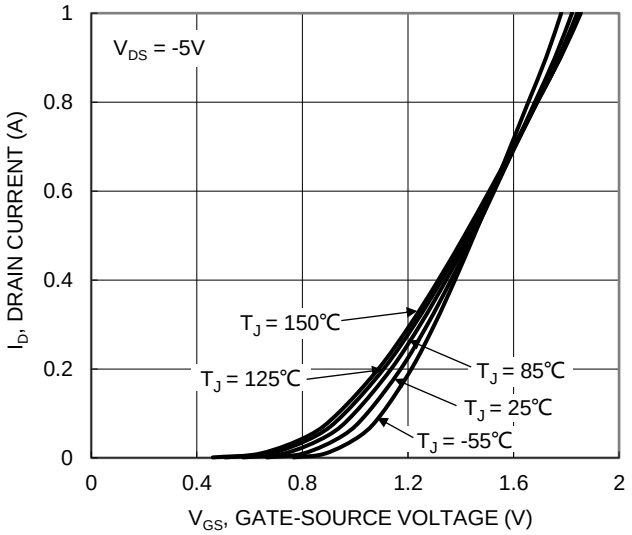


Figure 14. Typical Transfer Characteristic

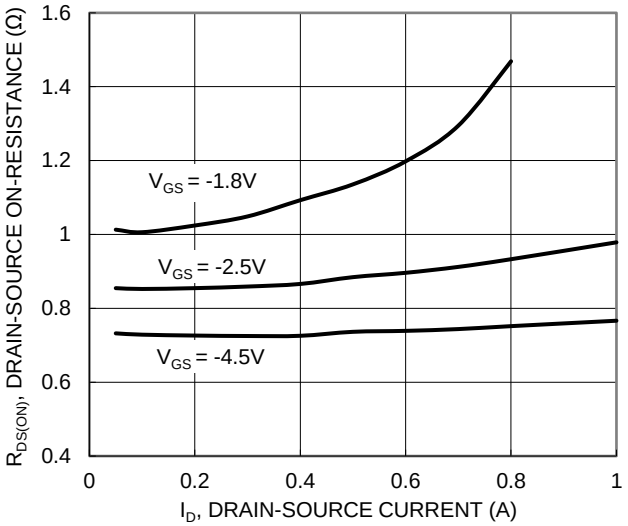


Figure 15. Typical On-Resistance vs. Drain Current and Gate Voltage

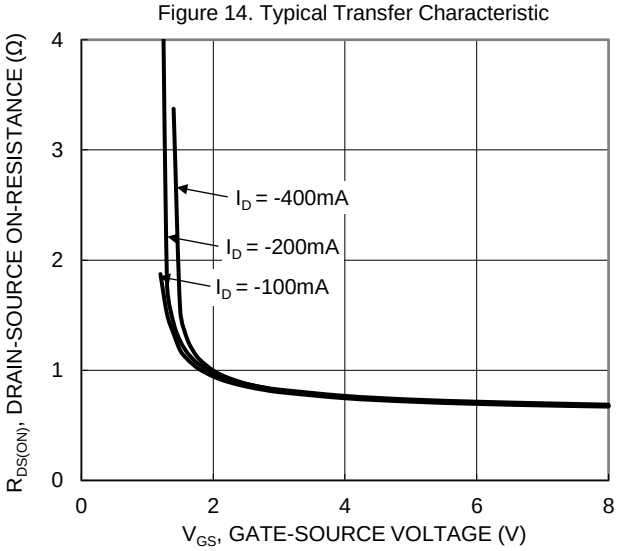


Figure 16. Typical Transfer Characteristic

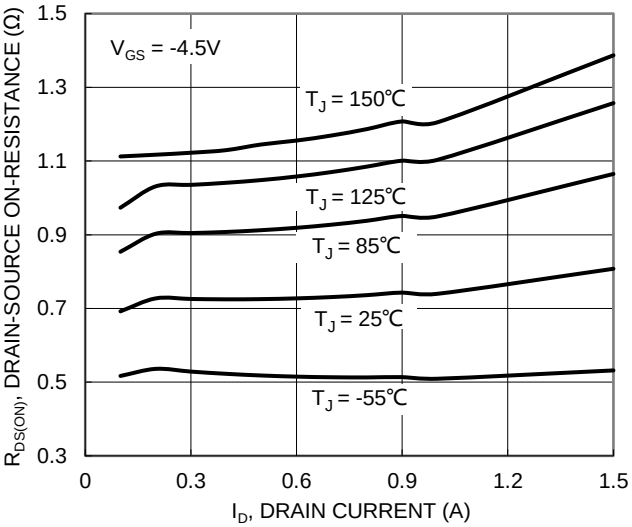


Figure 17. Typical On-Resistance vs. Drain Current and Junction Temperature

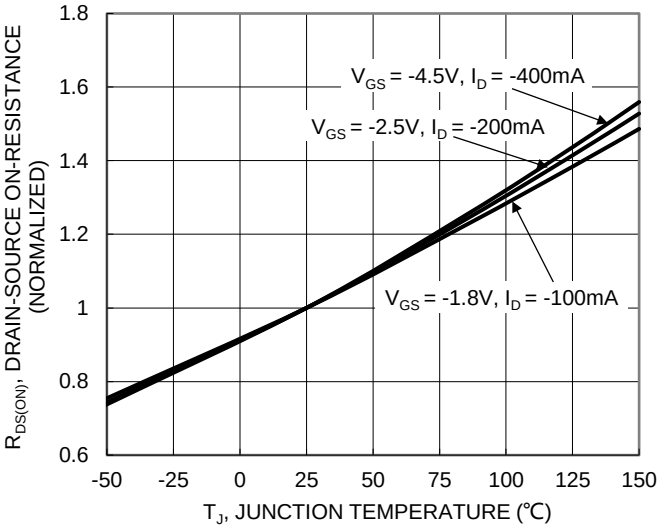


Figure 18. On-Resistance Variation with Junction Temperature

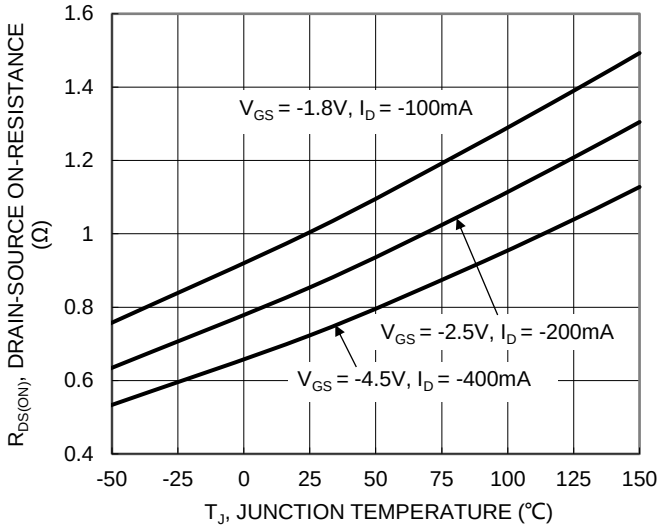


Figure 19. On-Resistance Variation with Junction Temperature

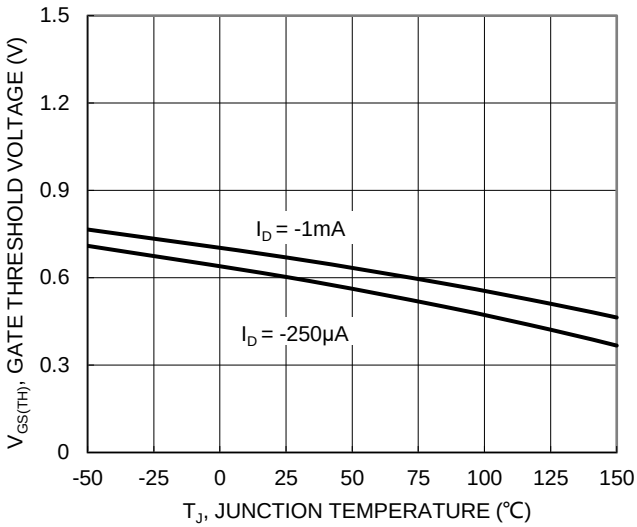


Figure 20. Gate Threshold Variation vs. Junction Temperature

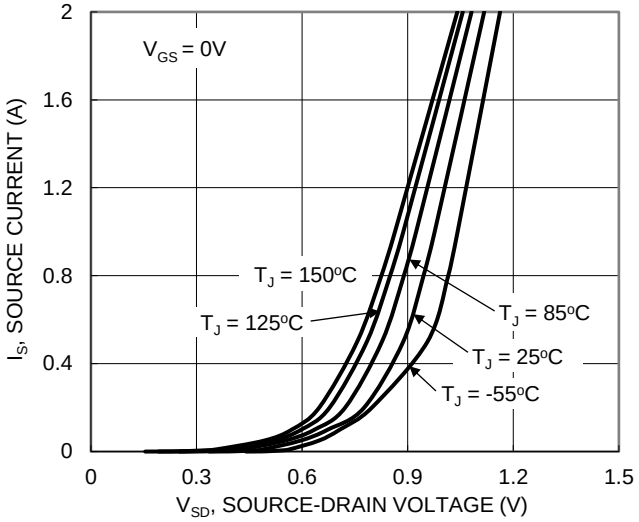


Figure 21. Diode Forward Voltage vs. Current

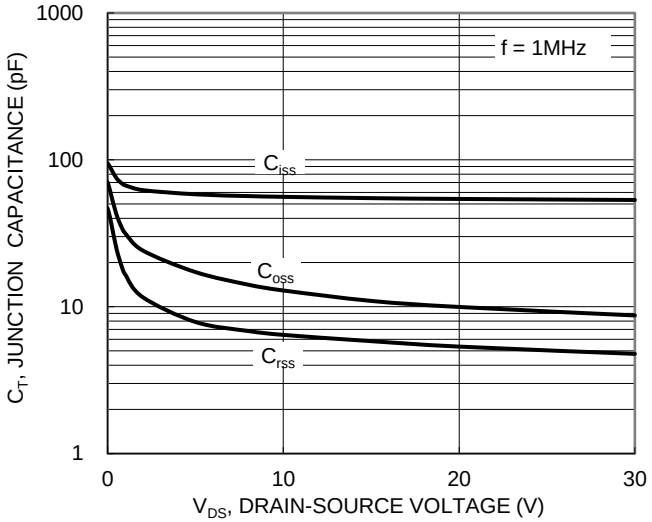


Figure 22. Typical Junction Capacitance

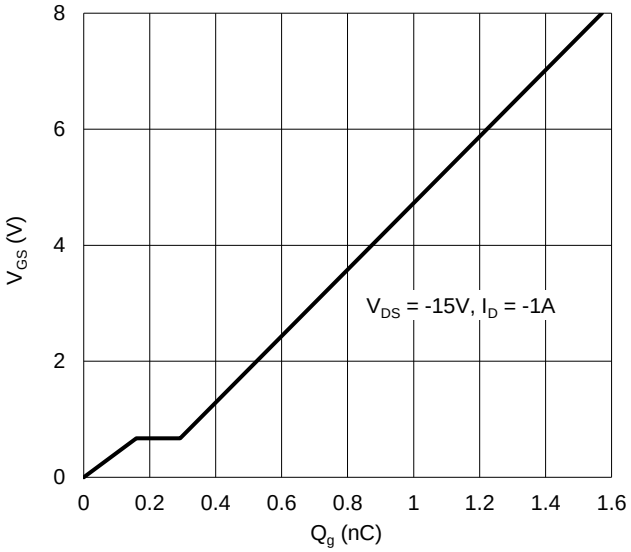


Figure 23. Gate Charge

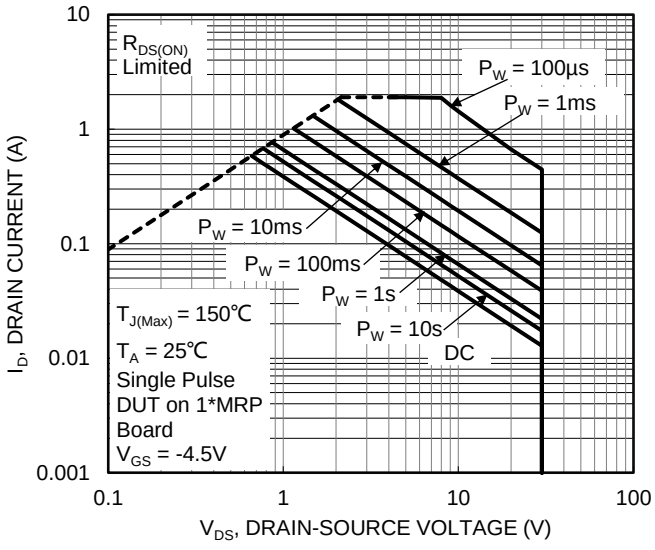


Figure 24. SOA, Safe Operation Area

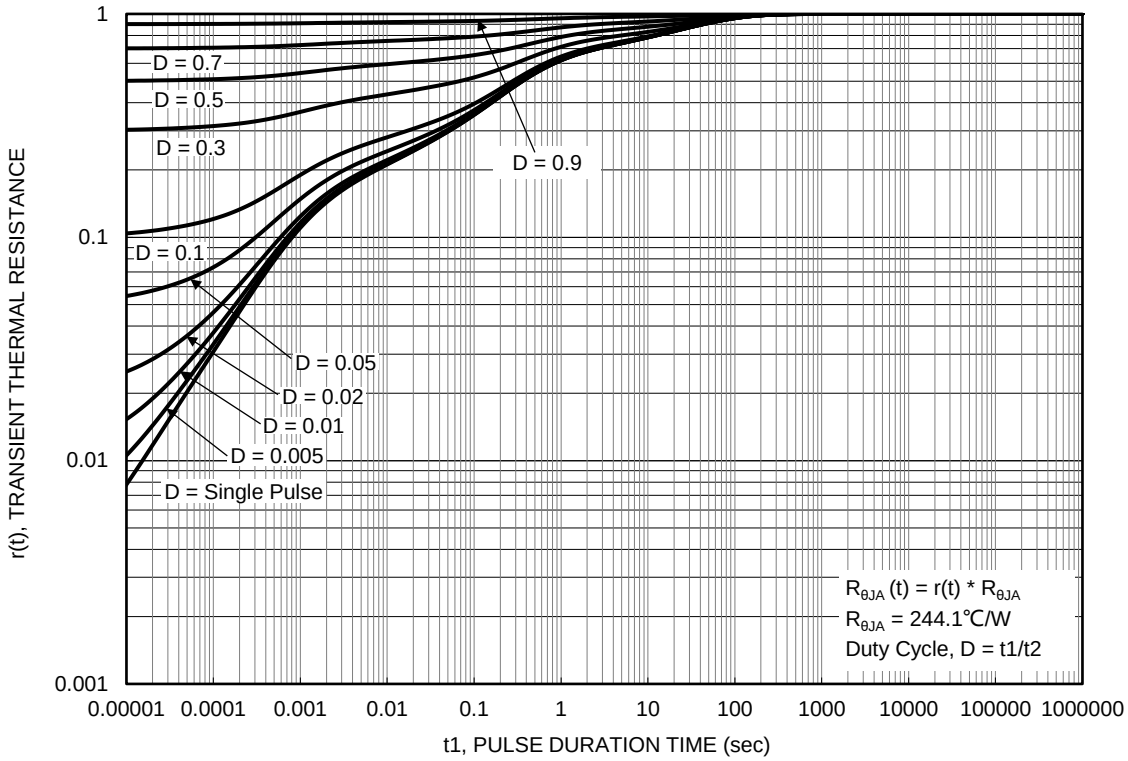
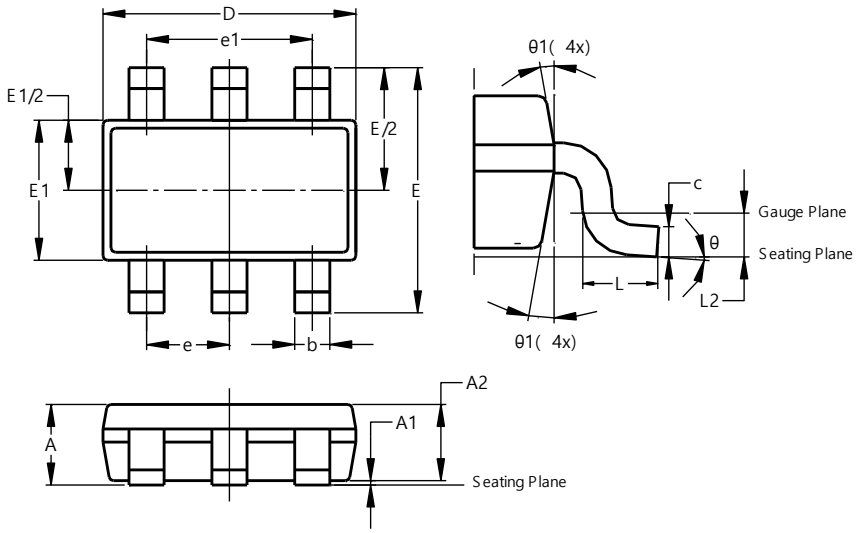


Figure 25. Transient Thermal Resistance

Package Outline Dimensions

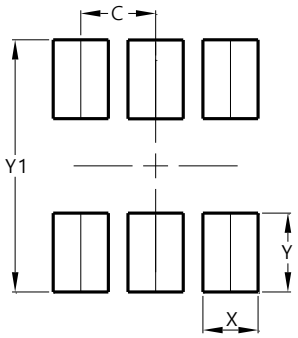
TSOT26



TSOT26			
Dim	**Min**	**Max**	**Typ**
A	–	1.00	–
A1	0.010	0.100	–
A2	0.840	0.900	–
D	2.800	3.000	2.900
E	2.800 BSC		
E1	1.500	1.700	1.600
b	0.300	0.450	–
c	0.120	0.200	–
e	0.950 BSC		
e1	1.900 BSC		
L	0.30	0.50	–
L2	0.250 BSC		
θ	0°	8°	4°
θ1	4°	12°	–
All Dimensions in mm			

Suggested Pad Layout

TSOT26



Dimensions	Value (in mm)
C	0.950
X	0.700
Y	1.000
Y1	3.200